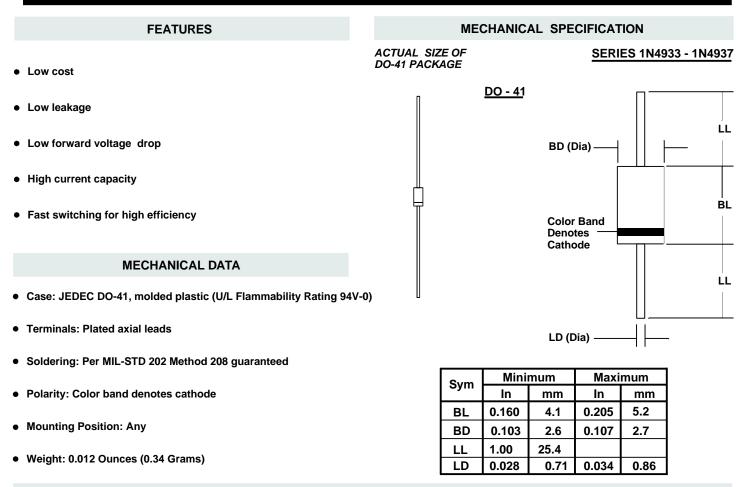


1 AMP FAST RECOVERY SILICON DIODES



MAXIMUM RATINGS & ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive loads, derate current by 20%.

PARAMETER (TEST CONDITIONS)	SYMBOL	RATINGS					UNITS
Series Number		1N4933	1N4934	1N4935	1N4936	1N4937	
Maximum DC Blocking Voltage	Vrм	50	100	200	400	600	VOLTS
Maximum RMS Voltage	Vrms	35	70	140	280	420	
Maximum Peak Recurrent Reverse Voltage	Vrrm	50	100	200	400	600	
Average Forward Rectified Current @ TA = 75 °C, Lead length = 0.375 in. (9.5 mm)	lo	1					AMPS
Peak Forward Surge Current (8.3 mSec single half sine wave superimposed on rated load)	IFSM	30					
Maximum Forward Voltage at 1 Amp DC	Vfm	1.2					VOLTS
Maximum Reverse Recovery Time (IF=1A, VR=30V - See Fig. 5)	Trr	200					nS
Maximum Average DC Reverse Current@ TA = 25°CAt Rated DC Blocking Voltage@ TA = 100°C	Irm	5 100					μΑ
Typical Thermal Resistance, Junction to Ambient (Note 1)	RθJA	41					°C/W
Typical Junction Capacitance (Note 2)	CJ	15					pF
Operating and Storage Temperature Range	TJ, TSTG	-65 to +175					°C

NOTES: (1) Thermal resistance from junction to ambient with diode mounted on PC Board and lead lengths = 0.375 in. (9.5 mm) (2) Measured at 1MHz & applied reverse voltage of 4 volts



1 AMP FAST RECOVERY SILICON DIODES

RATING & CHARACTERISTIC CURVES FOR SERIES 1N4933 - 1N4937

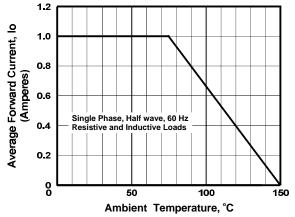
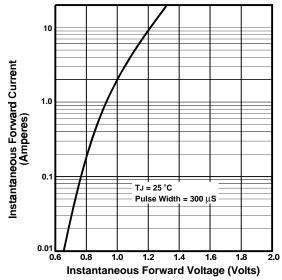


FIGURE 1. FORWARD CURRENT DERATING CURVE





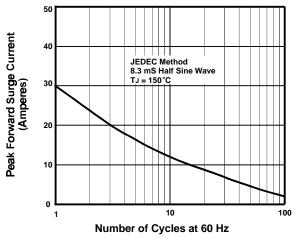
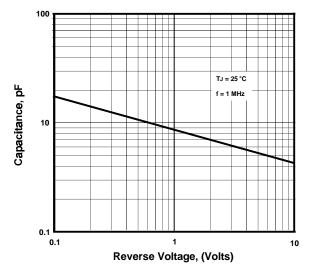
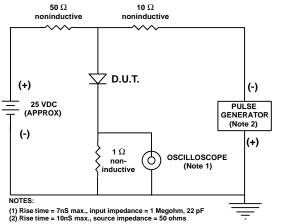


FIGURE 2. MAXIMUM NON-REPETITIVE SURGE CURRENT





4.97bfsdp101



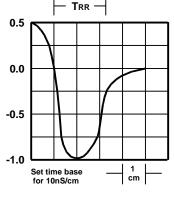


FIGURE 5. REVERSE RECOVERY TEST SETUP AND TIME CHARACTERISTIC